

MEMORY DEVICE

ABSTRACT

According to one embodiment, a memory device is configured to execute an efficient read operation is provided. The memory device includes a plurality of memory cells, a word line, and a controller. Each of the memory cells stores first to fifth bit data based on the threshold voltage. The memory cells store a first page to a fifth page respectively corresponding to the first bit data to the fifth bit data. A word line is coupled to the memory cells. A controller executes a read operation for reading data from the memory cells by applying a read voltage to the word line. Numbers of times the controller applies read voltages different from one another to the word line in read operations for the first page to the fifth page are 7, 6, 6, 6, and 6, respectively.

FIG.1